



GSX4020T

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

Trench MOSFET

40V Normal Power Transistor

GSX4020T

Data Sheet

Ver 1.0

2017-3-20

40V 20APower MOSFET

Description

GroupSemiconductor(GS) has series Trench power MOSFET platforms for voltage up 20V to 200 volts, both with design service and manufacturing capability, including cell, termination design and simulation.

The GS 40V 20A power MOSFET is a Low voltage N channel Trench power MOSFET sample with advanced technology to have better characteristics, such as fast switching time, low Ciss and Crss, low on resistance and excellent avalanche characteristics, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

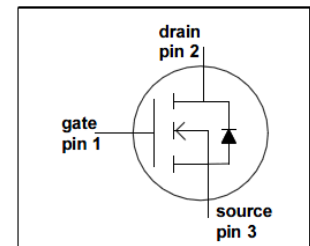
$R_{DS(ON)} < 19m\ \Omega$ @ $V_{GS} = 10V$

$V_{DS} = 40V$

I_D (@ $V_{GS}=10V$) = 20A

PKG

GSS4020T	GSD4020T	GSA4020T	GSP4020T	GSB4020T
TO-251	TO-252	TO-220Fullpak	TO-220	TO-263



Absolute Maximum Ratings (TC = 25° C, unless otherwise specified)

Symbol	Parameter	Maximum	Units
VDS	Drain-Source Voltage	40	V
VGS	Gate-Source Voltage	±20	V
ID ⁽¹⁾	Continuous Drain Current (TC=25° C)	20	A
	Continuous Drain Current (TC=100° C)	14	
IDM ⁽²⁾	Pulsed Drain Current	80	A

40V 20APower MOSFET

EAR ^{(2),(3)}	Repetitive avalanche energy	29	mJ
EAS ⁽⁴⁾	Single pulsed avalanche energy (1mH)	120	mJ
dv/dt	Peak diode recovery dv/dt	5	V/ns
PD ⁽¹⁾	Power Dissipation (TC=25° C) TO-220	80	W
	Derating above 25° C	1.5	W/ ° C
TJ	Max. operating junction temperature	150	° C
TSTG	Storage temperature	-55 to +150	° C

■ Thermal Characteristics

Symbol	Parameter	Value (TO220)	Unit
R _{θJA} ⁽⁶⁾	Maximum Junction-to-Ambient	82	C/W
R _{θCS} ⁽⁶⁾	Maximum Case-to-sink	0.6	C/W
R _{θJC} ^{(7),(8)}	Maximum Junction-to-Case θ	4.1	C/W

1. The power dissipation PD is based on TJ(MAX)=150° C in a TO-251 package, using junction-to-case thermal resistance.
2. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150° C.
3. L=1mH, Starting TJ=25° C.
4. L = 10mH, starting TJ = 25° C.
5. L=60mH, starting TJ = 25° C.
6. The tests are performed with the device with T A =25° C.
7. The R _{θJA} is the sum of the thermal impedance from junction to case R _{θJC} and case to ambient.
8. These curves are based on the junction-to-case thermal impedance, assuming a maximum junction temperature of TJ(MAX)=150° C.

40V 20A Power MOSFET

■ Electrical Characteristics (T_J=25° C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BVDSS	Drain-Source Breakdown Voltage	ID=250uA, VGS=0V, T _J =25° C	40			V
BVDSS /ΔT _J	Zero Gate Voltage Drain Current	ID=250uA, VGS=0V		0.72		V/° C
IDSS	Zero Gate Voltage Drain Current	VDS=40V, VGS=0V			1	uA
		VDS=40V, T _J =125° C	10			
IGSS	Gate-Body leakage current	VDS=0V, VGS=20V			100	nA
		VDS=0V, VGS=-20V	-100			
On Characteristics						
VGS(th)	Gate Threshold Voltage	VDS=Vgs, ID=250uA	1.1	1.4	2.0	V
RDS(ON)	Static Drain-Source On-Resistance	VGS=10V, ID=20A		0.015	0.019	Ω
gFS	Forward Transconductance	VDS = 5 V, ID = 15A		40		S
Source Drain Diode Characteristics						
VSD	Diode Forward Voltage	IS=20A, VGS=0V		0.82	1.2	V
ISD	Continuous source-drain Current			30		A
trr	Reverse Recovery Time	IF=20A, dI/dt=100A/us		13		ns
Qrr	Reverse Recovery Charge	IF=20A, dI/dt=100A/us		30		nC
Dynamic Characteristics						
Ciss	Input Capacitance	VGS=0V, VDS=15V, f=1MHz		870		pF
Coss	Output Capacitance	VGS=0V, VDS=15V, f=1MHz		120		pF
Crss	Reverse Transfer Capacitance	VGS=0V, VDS=15V, f=1MHz		60		pF
Qg	Total Gate Charge	VDS=10V, ID=10A		15		nC
Qgs	Gate Source Charge	VDS=10V, ID=10A		3		nC
Qgd	Gate Drain Charge	VDS=10V, ID=10A		3.5		nC
Switching Characteristics						
t _d (on)	Turn-On DelayTime	VGS=10V, VDS=10V, ID=15A, RG=2.5 Ω		6		ns
tr	Turn-On Rise Time			12		ns
t _d (off)	Turn-Off DelayTime			26		ns
tf	Turn-Off Fall Time			6		ns

40V 20APower MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

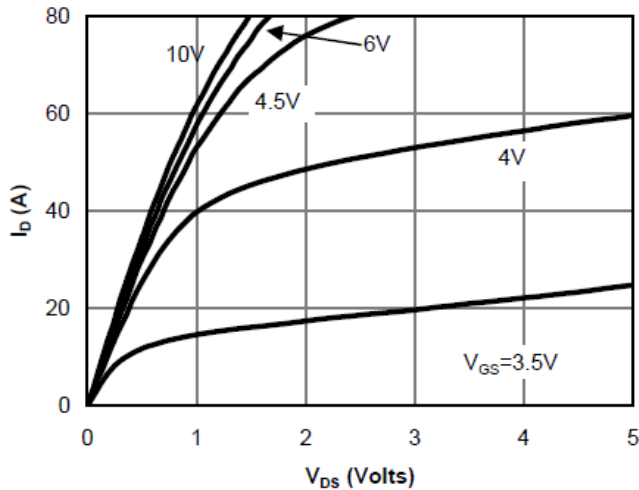


Fig 1: On-Region Characteristics (Note E)

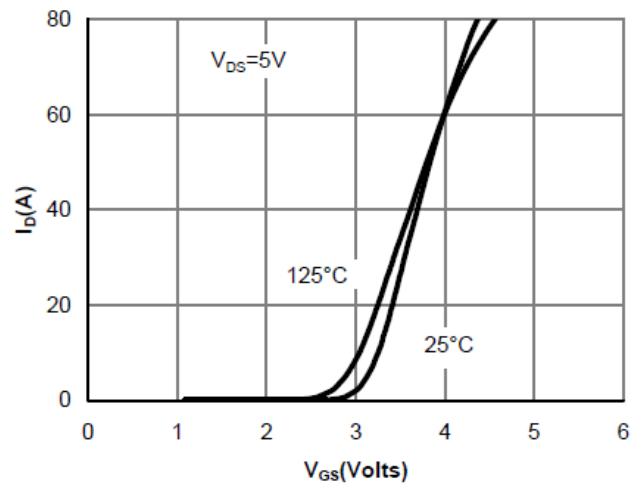


Figure 2: Transfer Characteristics (Note E)

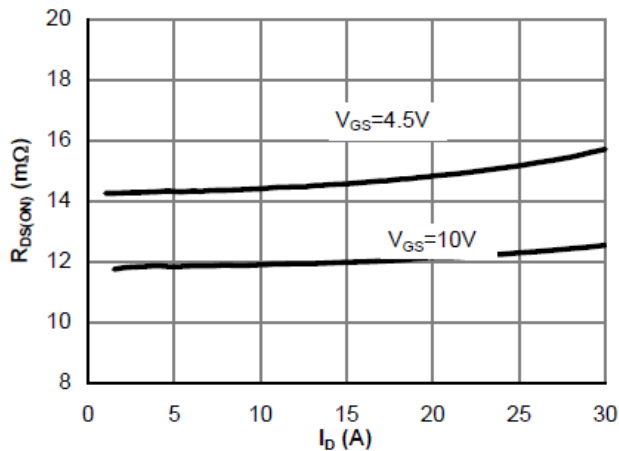


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

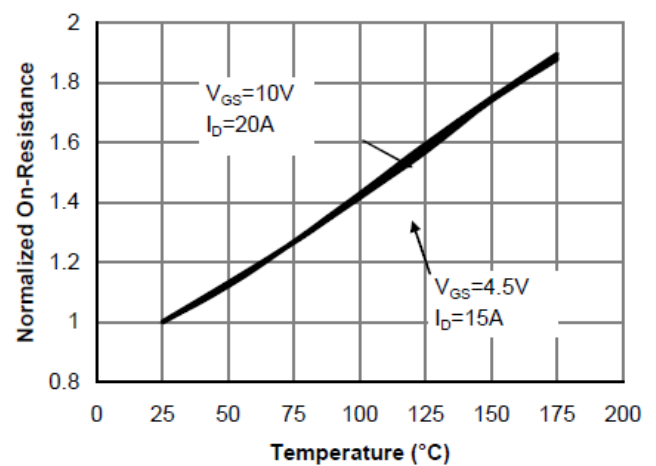


Figure 4: On-Resistance vs. Junction Temperature (Note E)

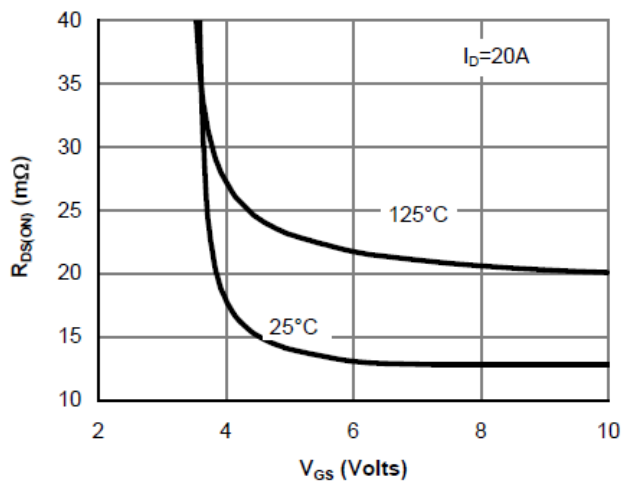


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

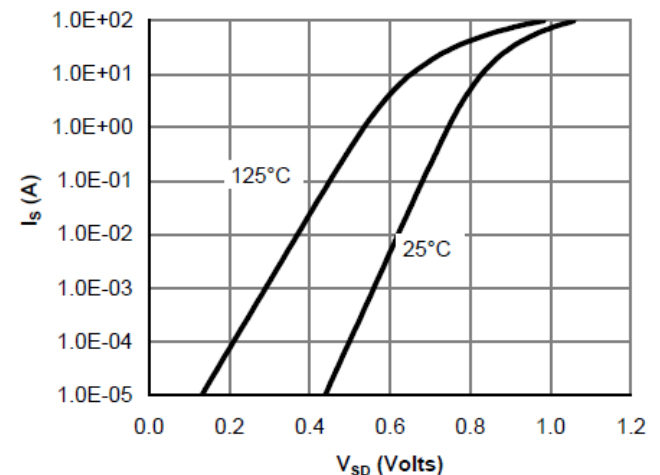


Figure 6: Body-Diode Characteristics (Note E)

40V 20A Power MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

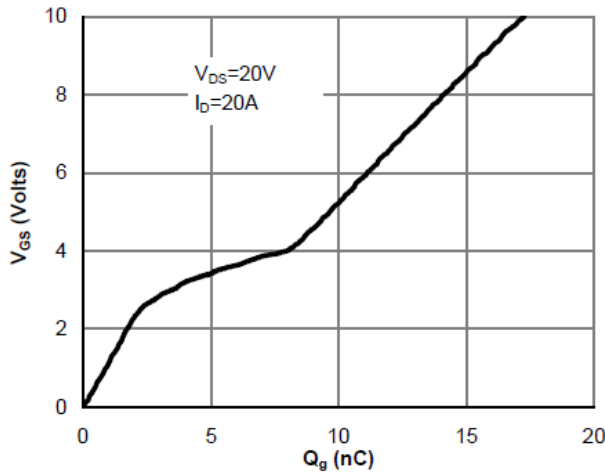


Figure 7: Gate-Charge Characteristics

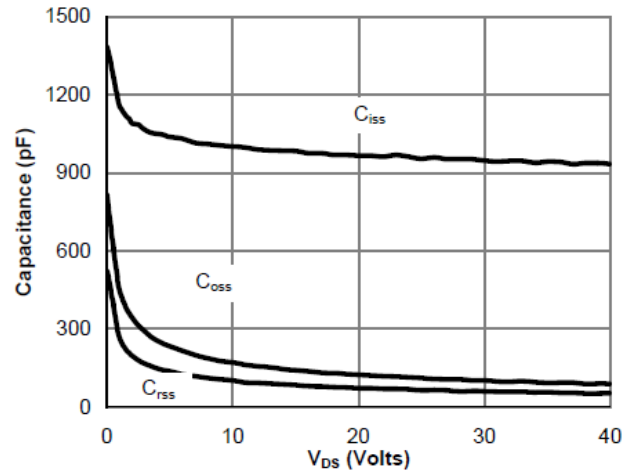


Figure 8: Capacitance Characteristics

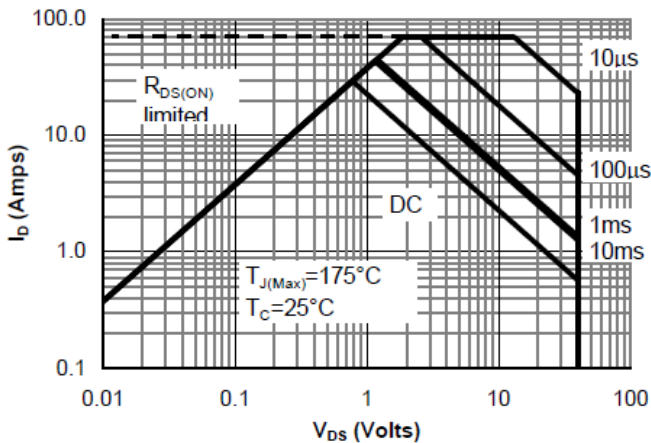


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

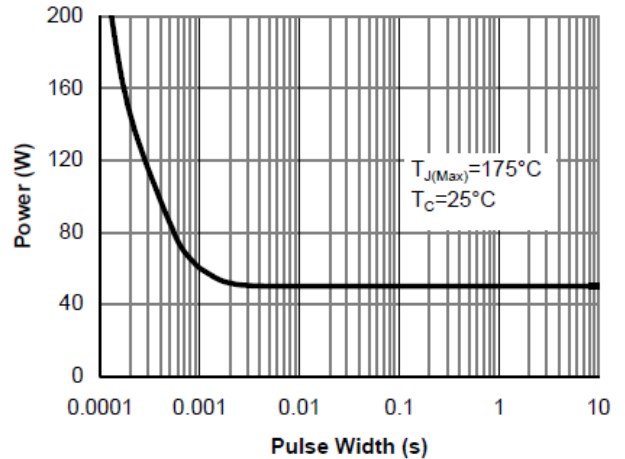


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

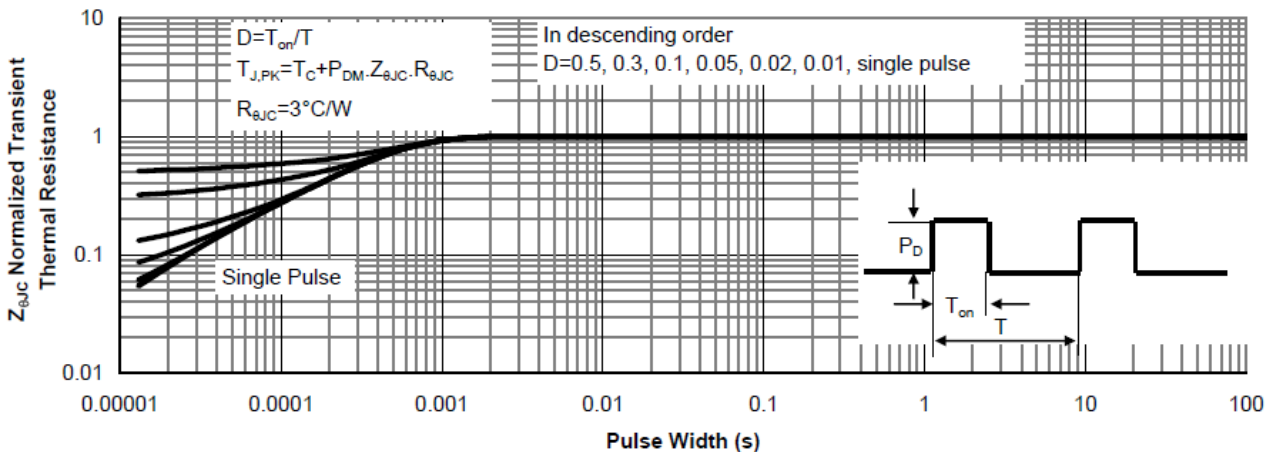


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

40V 20A Power MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

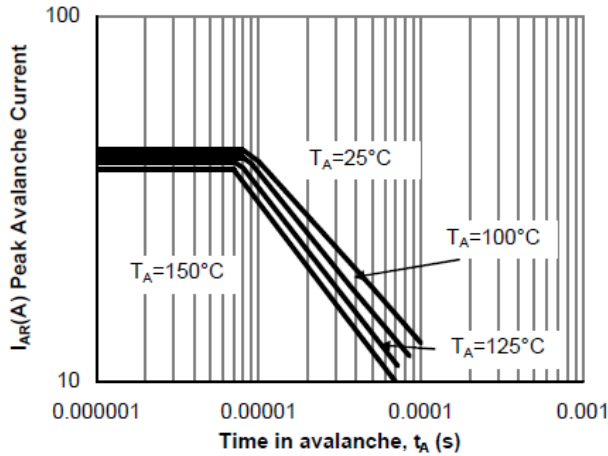


Figure 12: Single Pulse Avalanche capability (Note G)

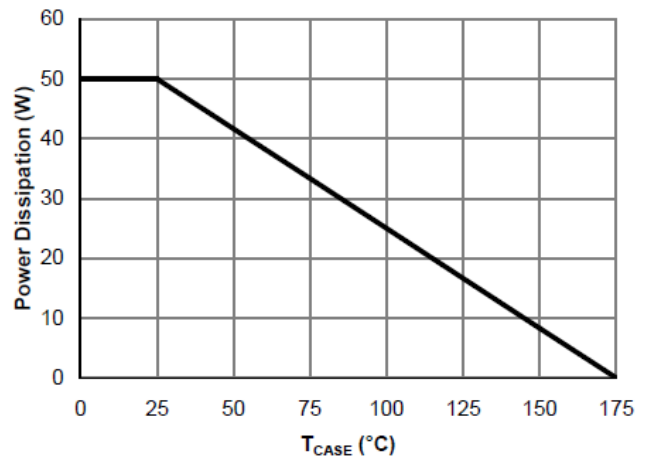


Figure 13: Power De-rating (Note F)

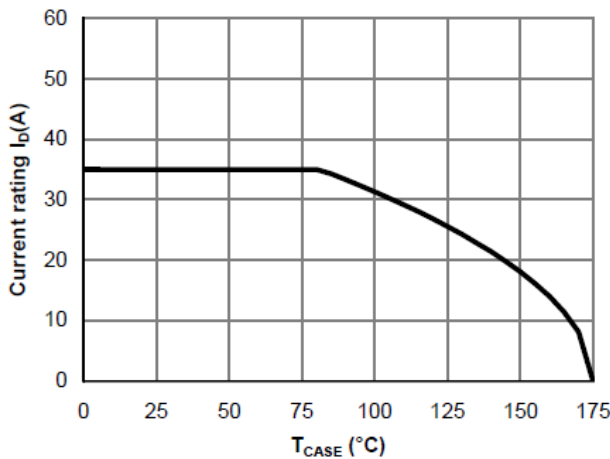


Figure 14: Current De-rating (Note F)

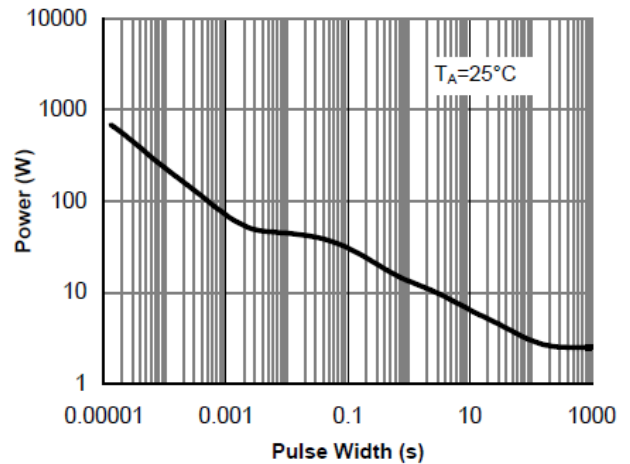


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

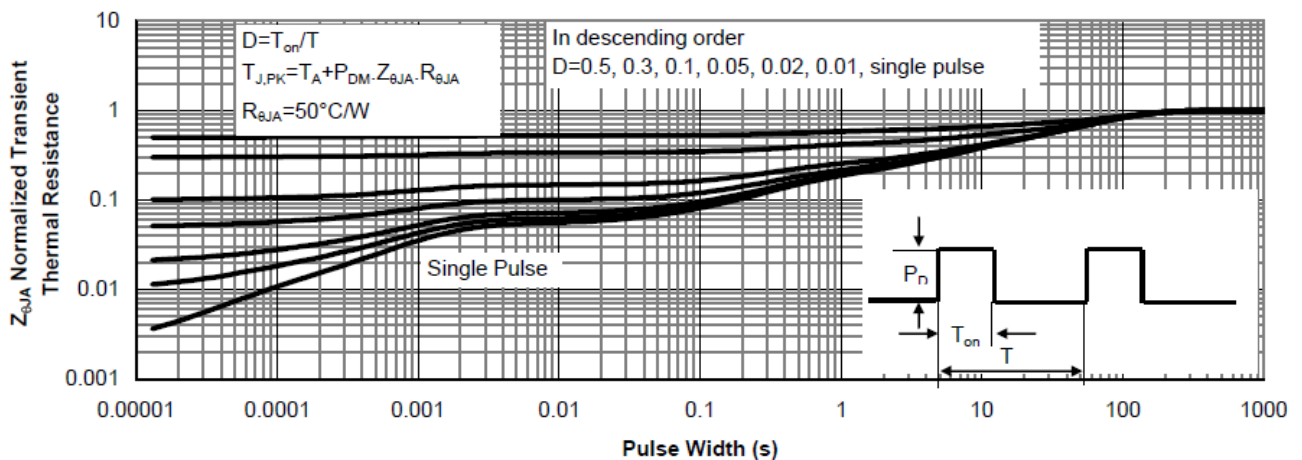


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

40V 20A Power MOSFET

Table 20 Switching times test circuit and waveform for inductive load

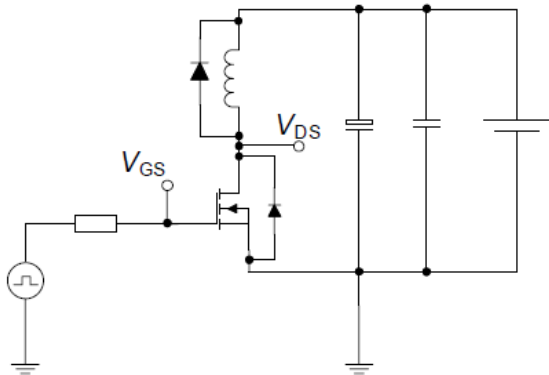
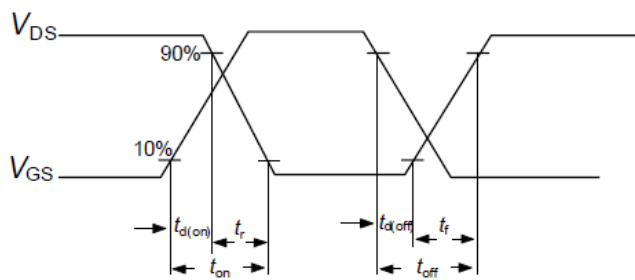
Switching times test circuit for inductive load	Switching time waveform
	

Table 21 Unclamped inductive load test circuit and waveform

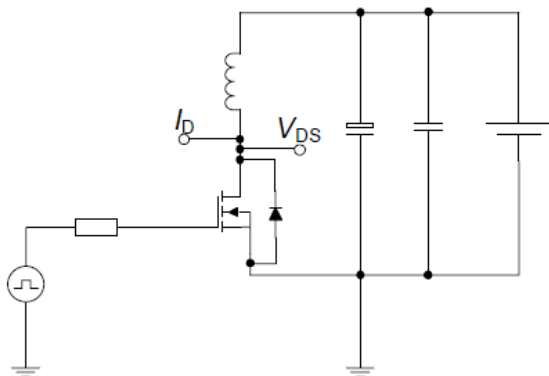
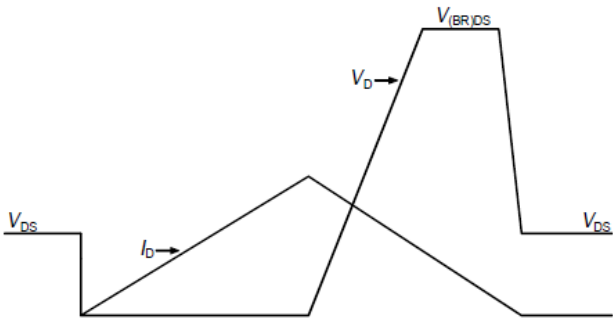
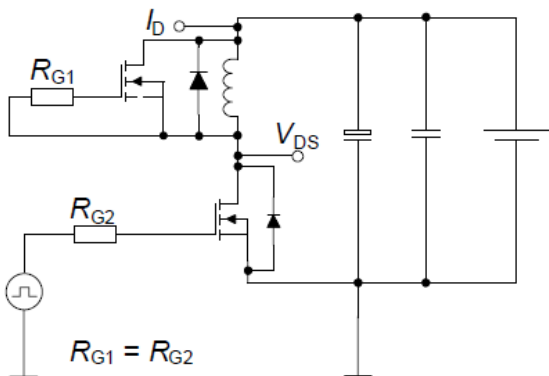
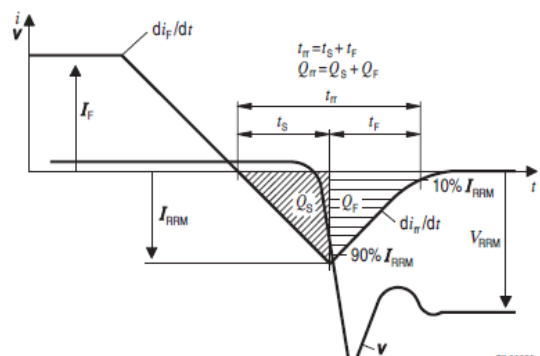
Unclamped inductive load test circuit	Unclamped inductive waveform
	

Table 22 Test circuit and waveform for diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
 $R_{G1} = R_{G2}$	 $t_{rr} = t_s + t_r$ $Q_{rr} = Q_s + Q_F$